


 PTO/US/OA/01 (08-03)
 Approved for use through 07/31/2006. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/BI/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Application Number	10/579,211 - Conf.# 6592
				Filing Date	May 12, 2006
				First Named Inventor	Toshihiko Shirasagi
				Art Unit	1756
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	SON-3162

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code* - Number* - Kind Code* (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ²

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
	CA	N. Koshida et al., "50-nm Metal Line Fabrication by Focused Ion Beam and Oxide Resists," Japanese Journal of Applied Physics, Vol. 30, No. 11B, November 1991, pp. 3246-3249			
	CB	S. M. Gorwadkar et al., "SiO ₂ /Si Bilayer Electron-Beam Resist Process for Nano-Fabrication," Japanese Journal of Applied Physics, Vol. 35 (1996), Part 1, No. 12B, pp. 6673-6678, December 1996			
	CC	S. A. Kostyukovich, "Investigations and modeling of physical processes in inorganic resists for the use in UV and laser lithography," Institute of Physics of Semiconductors, National Academy of Sciences Prospect Nauki 45, Kiev, 252028, UKRAINE, part of the SPIE Conference on Inorganic Optical Materials, California, SPIE Vol. 3424, July 1998			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	/Anna Verderame/	Date Considered	/Anna Verderame/
--------------------	------------------	-----------------	------------------

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /A.V./